

The CL - 211 is a high - power GaAlAs IRED mounted in a durable, hermetically sealed TO - 18 metal can package. The output power is high compared to GaAs IREDS.

FEATURES

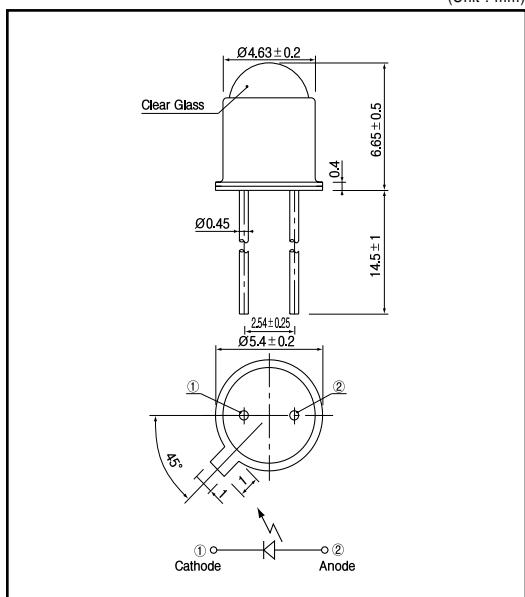
- High output power
- High reliability

APPLICATIONS

- Optical switches
- Transportation sensors

DIMENSIONS

(Unit : mm)



MAXIMUM RATINGS

(Ta=25)

Item	Symbol	Rating	Unit
Reverse voltage	V _R	4	V
Forward current	I _F	50	mA
Power dissipation	P _D	70	mW
Pulse forward current ^{*1}	I _{FP}	0.5	A
Operating temp.	T _{opr.}	- 30 + 85	
Storage temp.	T _{stg.}	- 40 + 100	
Soldering temp. ^{*2}	T _{sol.}	260	

^{*1}. pulse width : tw 100 μ sec. period : T=10msec.

^{*2}. For MAX.5 seconds at the position of 2 mm from the package

ELECTRO-OPTICAL CHARACTERISTICS

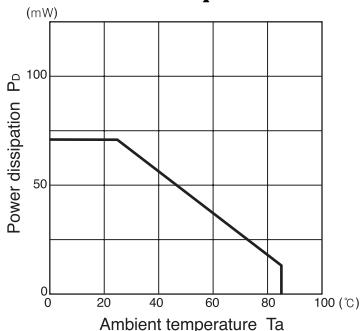
(Ta=25)

Item	Symbol	Conditions	Min.	Typ.	Max.	Unit.
Forward voltage	V _F	I=20mA		1.3	1.6	V
Reverse current	I _R	V _R =4V			10	μ A
Peak emission wavelength	λ	I=20mA		870		nm
Spectral bandwidth		I=20mA		45		nm
Radiant intensity	P _O	I=20mA		90		mV
Half angle				± 12		deg.

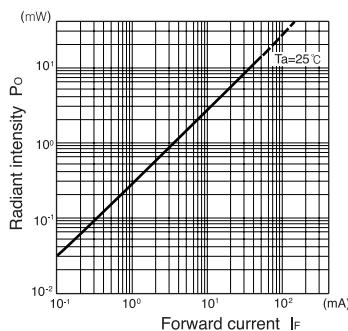
Infrared Emitting Diodes(GaAlAs)

CL - 211

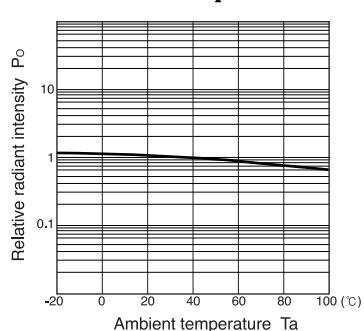
**Power dissipation Vs.
Ambient temperature**



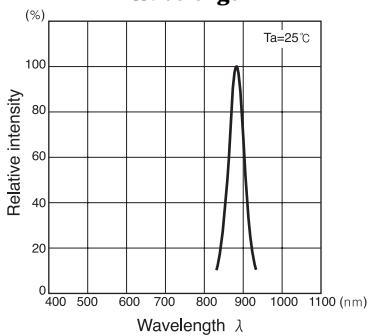
**Radiant intensity Vs.
Forward current**



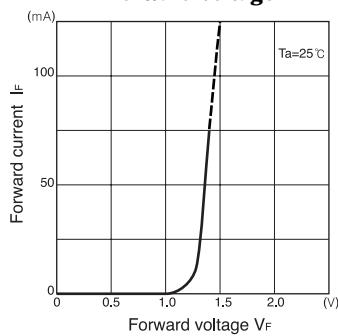
**Relative radiant intensity Vs.
Ambient temperature**



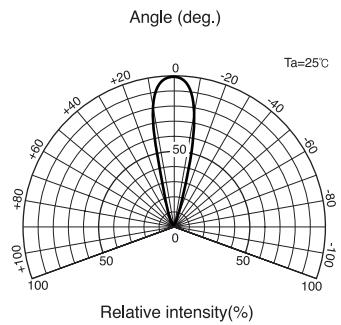
**Relative intensity Vs.
Wavelength**



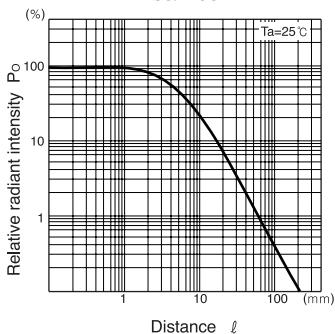
**Forward current Vs.
Forward voltage**



Radiant Pattern



**Relative radiant intensity Vs.
Distance**



Relative radiant intensity Vs.
Distance test method

